

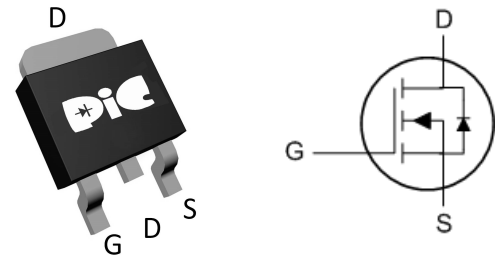
➤ General Description

This PAN00TX08X N-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent $R_{ds(On)}$ performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

➤ Feature

- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

➤ TO-252



➤ Application

- Switch application
- DC/DC Converters Power
- Tools

➤ Absolute Maximum Ratings

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current, $V_{GS} @ 10V_1$	$I_D @ T_C=25^\circ C$	5.4	A
Continuous Drain Current, $V_{GS} @ 10V_1$	$I_D @ T_C=100^\circ C$	3.4	A
Continuous Drain Current, $V_{GS} @ 10V_1$	$I_D @ T_A=25^\circ C$	1.7	A
Continuous Drain Current, $V_{GS} @ 10V_1$	$I_D @ T_A=70^\circ C$	1.3	A
Pulsed Drain Current ²	I_{DM}	11	A
Total Power Dissipation ³	$P_D @ T_C=25^\circ C$	20.8	W
Total Power Dissipation ³	$P_D @ T_A=25^\circ C$	2	W
Storage Temperature Range	T_{STG}	-55 to 150	$^\circ C$
Operating Junction Temperature Range	T_J	-55 to 150	$^\circ C$
Thermal Resistance Junction-ambient ¹	$R_{\theta JA}$	62	$^\circ C/W$
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	6	$^\circ C/W$

➤ Electrical Characteristics ($T_J=25^\circ C$ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$, $I_D=250\mu A$	100	---	---	V
BVDSS Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	Reference to $25^\circ C$, $I_D=1mA$	---	0.0672	---	$V/^\circ C$
Static Drain-Source On-Resistance ²	$R_{DS(ON)}$	$V_{GS}=10V$, $I_D=5A$	---	---	310	m Ω
		$V_{GS}=4.5V$, $I_D=3A$	---	---	320	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1.0	---	2.5	V
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}$		---	-4.12	---	$mV/^\circ C$
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=80V$, $V_{GS}=0V$, $T_J=25^\circ C$	---	---	1	μA
		$V_{DS}=80V$, $V_{GS}=0V$, $T_J=55^\circ C$	---	---	5	
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
Forward Transconductance	g_{fs}	$V_{DS}=5V$, $I_D=3A$	---	5.4	---	S
Gate Resistance	R_g	$V_{DS}=0V$, $V_{GS}=0V$, $f=1MHz$	---	2.5	---	Ω
Total Gate Charge (10V)	Q_g	$V_{DS}=80V$, $V_{GS}=10V$, $I_D=5A$	---	9.6	---	nC
Gate-Source Charge	Q_{gs}		---	1.83	---	
Gate-Drain Charge	Q_{gd}		---	1.85	---	
Turn-On Delay Time	$T_{d(on)}$	$V_{DD}=50V$, $V_{GS}=10V$, $R_g=3.3$ $I_D=5A$	---	1.4	---	ns
Rise Time	T_r		---	30.6	---	
Turn-Off Delay Time	$T_{d(off)}$		---	11.2	---	
Fall Time	T_f		---	6	---	
Input Capacitance	C_{iss}	$V_{DS}=15V$, $V_{GS}=0V$, $f=1MHz$	---	508	---	pF
Output Capacitance	C_{oss}		---	29	---	
Reverse Transfer Capacitance	C_{rss}		---	16.4	---	

➤ Diode Characteristics

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Continuous Source Current ^{1,4}	I_S	$V_G=V_D=0V$, Force Current	---	---	5.4	A
Pulsed Source Current ^{2,4}	I_{SM}		---	---	11	A
Diode Forward Voltage ²	V_{SD}	$V_{GS}=0V$, $I_S=1A$, $T_J=25^\circ C$	---	---	1.2	V
Reverse Recovery Time	t_{rr}	$I_F=5A$, $dI/dt=100A/\mu s$, $T_J=25^\circ C$	---	20	---	nS
Reverse Recovery Charge	Q_{rr}		---	19	---	nC

Note :

1. Pulse width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. Ensure that the channel temperature does not exceed $150^\circ C$.
4. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

➤ Typical Characteristics

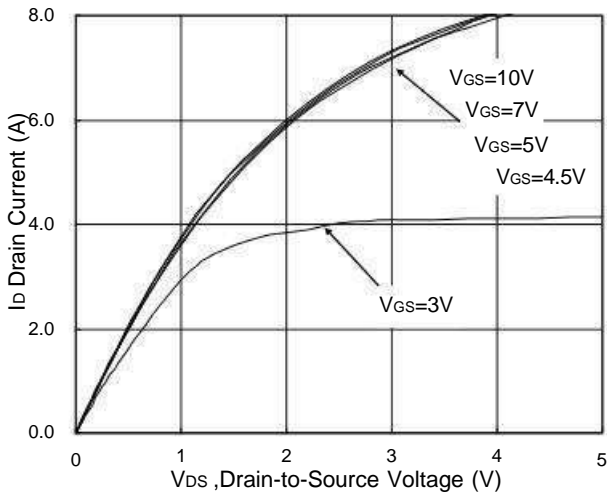


Fig.1 Typical Output Characteristics

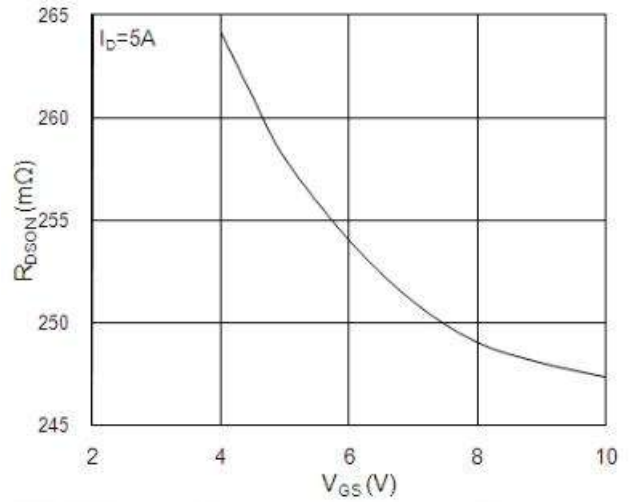


Fig.2 On-Resistance vs. Gate-Source

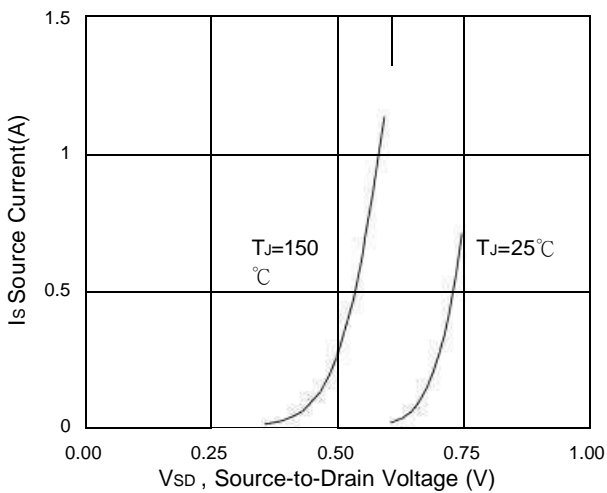


Fig.3 Forward Characteristics Of Reverse

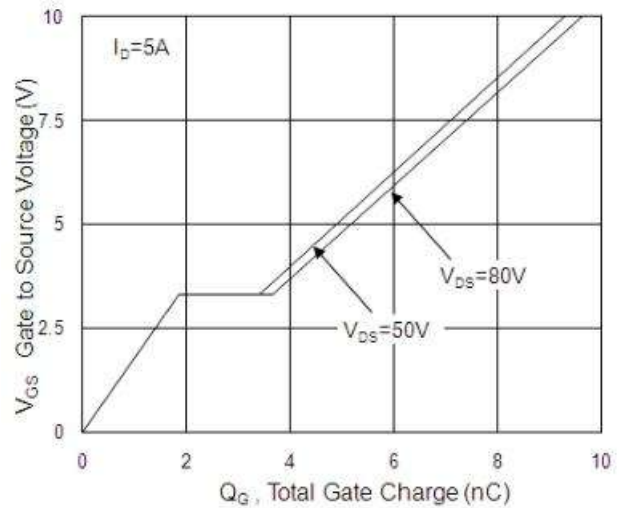


Fig.4 Gate-Charge Characteristics

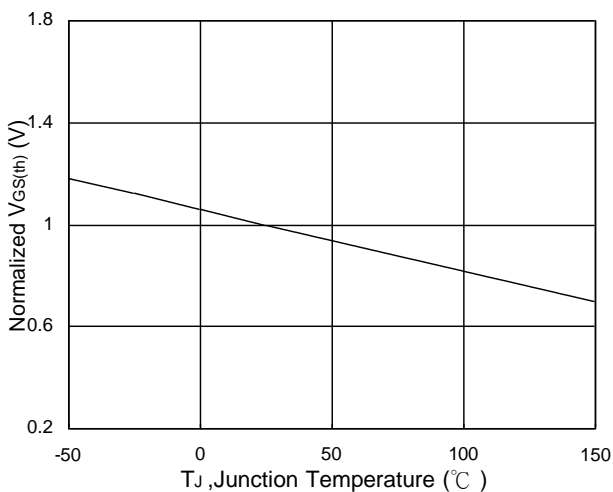


Fig.5 Normalized VGS(th) vs. Tj

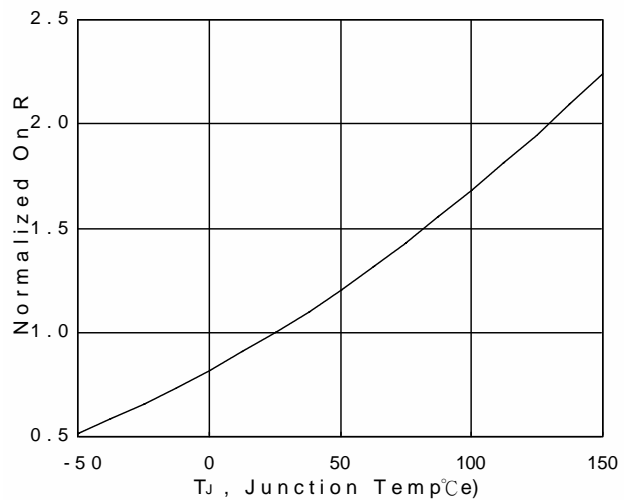


Fig.6 Normalized Rds(on) vs. Tj

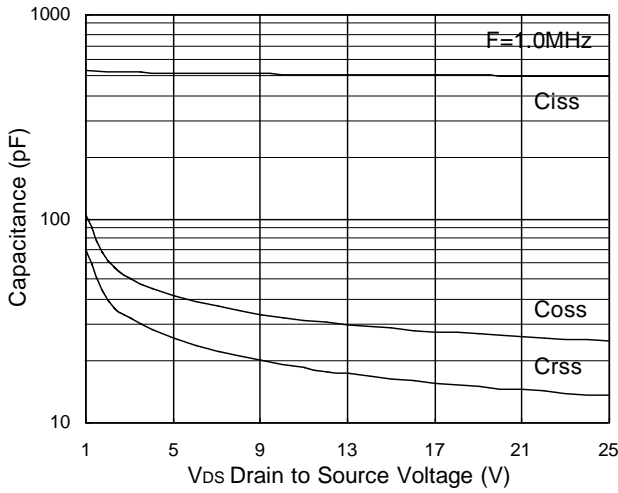


Fig.7 Capacitance

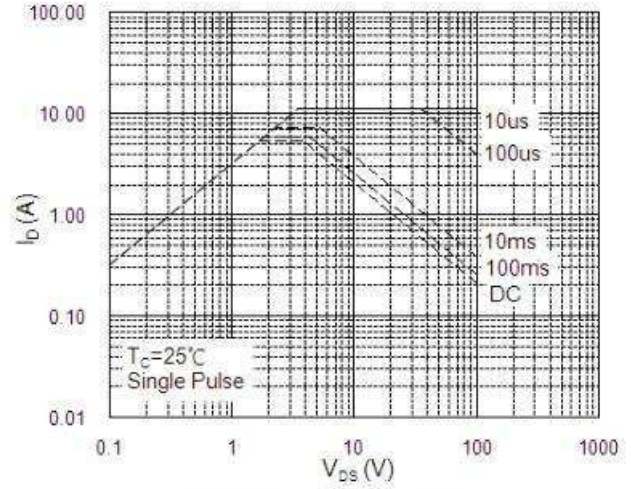


Fig.8 Safe Operating Area

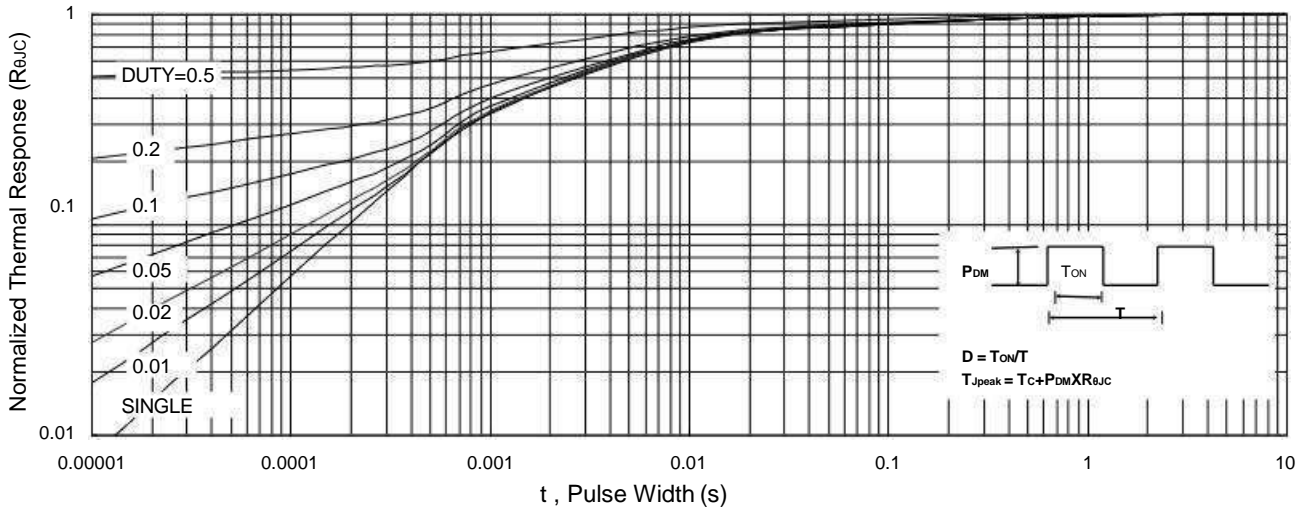


Fig.9 Normalized Maximum Transient Thermal Impedance

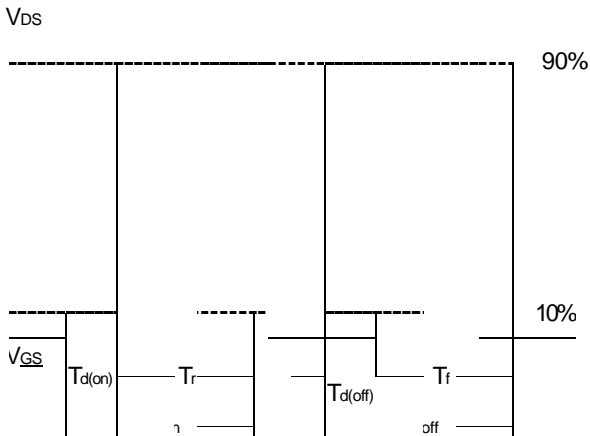


Fig.10 Switching Time Waveform

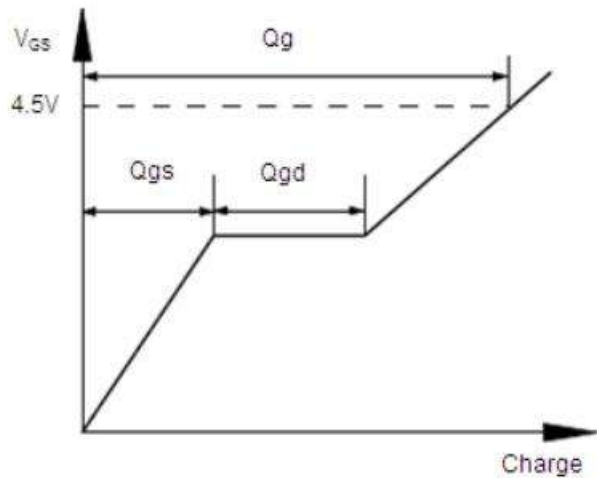


Fig.11 Gate Charge Waveform

➤ Recommend IR Reflow Soldering Thermal Profile

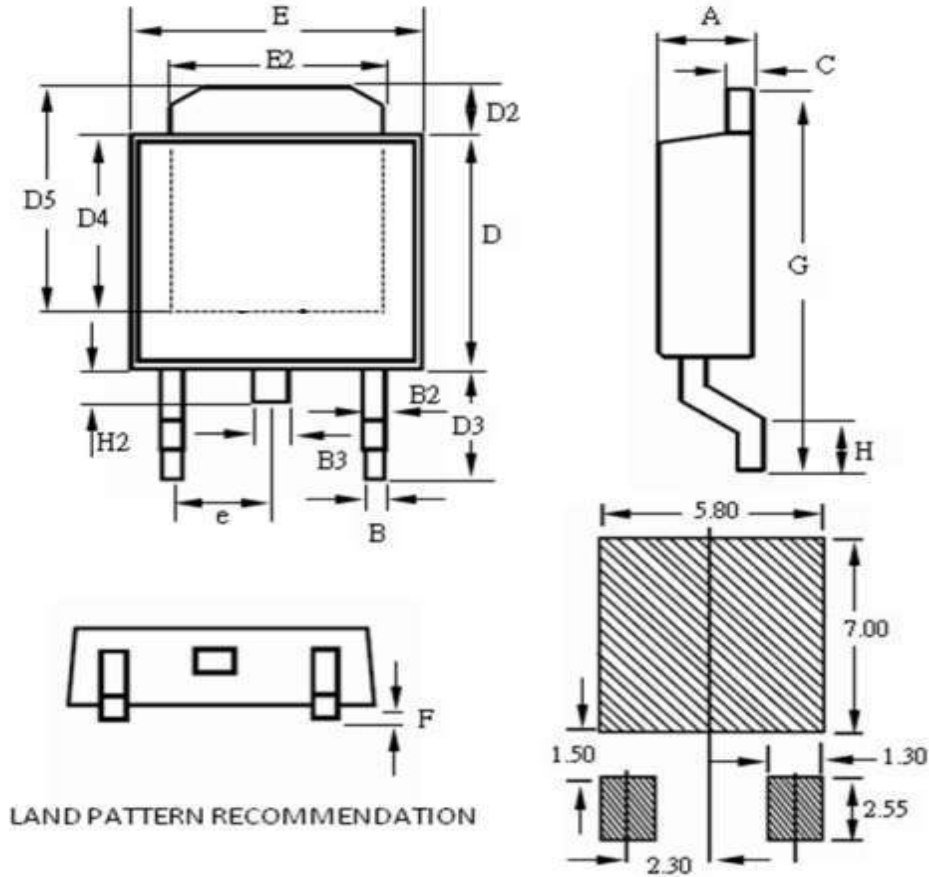


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T_{smin})	150°C
Temperature Max. (T_{smax})	200°C
Time (t_s) from (T_{smin} to T_{smax})	60-120 seconds
Average Ramp-up Rate (t_L to t_P)	3°C/second max.
Liquidous Temperature (T_L)	217°C
Time (t_L) Maintained Above (T_L)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (t_P) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (T_P to T_L)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➤ Ordering Information

Part Number	Description	Quantity
PAN00TX08X	TO-252 Reel	2500 pcs

➤ Package Information (TO-252)



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	2.10	--	2.50	0.083	--	0.098
B	0.30	--	0.89	0.012	--	0.035
B2	0.40	--	1.14	0.016	--	0.045
B3	0.60	--	1.00	0.024	--	0.039
C	0.40	--	0.89	0.016	--	0.035
D	5.30	--	6.25	0.209	--	0.246
D2	0.50	--	1.70	0.020	--	0.067
D3	2.20	--	3.40	0.087	--	0.134
D4	4.32	--	--	0.170	--	--
D5	5.21	--	--	0.205	--	--
E	6.30	--	6.73	0.248	--	0.265
E2	4.80	--	5.46	0.189	--	0.215
F	0.00	--	0.30	0.000	--	0.012
G	9.20	--	10.41	0.362	--	0.410
H	0.90	--	1.95	0.035	--	0.077
H2	0.50	--	1.10	0.020	--	0.043
e	--	2.30	--	--	0.091	--

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